Serial No.10/769,127 HP Docket No: 200209576-1

REMARKS

This communication is in response to the Office Action dated January 26, 2006. Claims 1-10, 13-20, 22 and 23 are pending in the present Application. Claims 11, 12, 21 and 24-30 have been withdrawn from consideration. Claims 1-10, 13-20, 22 and 23 are rejected.

§102 Rejections

Claims 1-10, 13-20, 22 and 23

For ease of review, Applicant reproduces independent claims 1 and 13 herein below:

- A method for forming a semiconductor device comprising: forming a 3-dimensional (3D) pattern in a substrate; and depositing at least one material over the substrate in accordance with desired characteristics of the semiconductor device.
- 13. A system for forming a semiconductor device comprising: means for forming a 3-dimensional (3D) pattern in a substrate; and

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